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(54) NANOTUBE SEMICONDUCTOR DEVICES

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(57) ABSTRACT

Semiconductor devices are formed using a thin epitaxial layer (nanotube) formed on sidewalls of dielectric-filled trenches. In one embodiment, a semiconductor device is formed in a first semiconductor layer having trenches and mesas formed thereon where the trenches extend from the top surface to the bottom surface of the first semiconductor layer. The semiconductor device includes semiconductor regions formed on the bottom surface of the mesas of the first semiconductor layer.

